MSKSEMI















ESD

TVS

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Broduct data sheet



FEATURES

- Switching and amplification in high voltage Applications such as telephony
- Low current(max. 600mA)
- High voltage(max.180V)

SOT-89



- 1. BASE
- 2. COLLECTOR
- 3. EMITTER

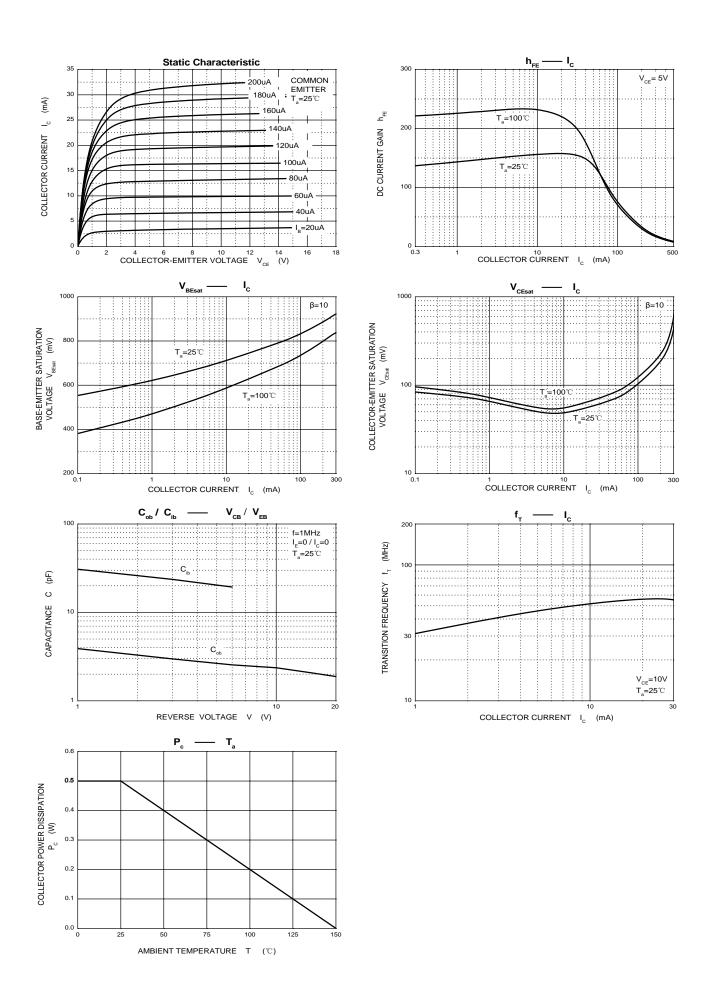
MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{СВО}	Collector-Base Voltage	180	V
V _{CEO}	Collector-Emitter Voltage	160	V
V _{EBO}	Emitter-Base Voltage	6	V
lc	Collector Current -Continuous	0.6	Α
Pc	Collector Power Dissipation	0.5	W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

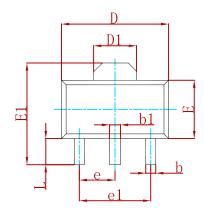
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100μ A,I _E =0	180			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA,I _B =0	160			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I _E =10 μ A,I _C =0	6			V
Collector cut-off current	I _{CBO}	V _{CB} =120V,I _E =0			50	nA
Emitter cut-off current	I _{EBO}	V _{EB} =4V,I _C =0			50	nA
	h _{FE(1)}	V _{CE} =5V,I _C =1mA	80			
DC current gain	h _{FE(2)}	V _{CE} =5V,I _C =10mA	100		300	
	h _{FE(3)}	V _{CE} =5V,I _C =50mA	30			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =10mA,I _B =1mA			0.15	V
Conector-enlitter Saturation Voltage	V _{CE(sat)}	I _C =50mA,I _B =5mA			0.2	٧
Base-emitter voltage	V _{BE(sat)}	I _C =10mA,I _B =1mA			1	V
Base-ennitter voltage	V _{BE(sat)}	I _C =50mA,I _B =5mA			1	٧
Transition frequency	f _T	V _{CE} =10V,I _C =10mA,f=100MHz	100			MHz
Collector output capacitance	C _{ob}	V _{CB} =10V,I _E =0,f=1MHz			6	pF
Noise figure	NF	V_{CE} =5V, I_c =0.2mA, f=10Hzto15.7KHZ,Rs=10 Ω			8	dB

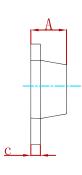
CXT5551 HF &





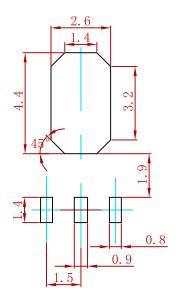
PACKAGE MECHANICAL DATA





Symbol	Dimensions In Millimeters		Dimensions In Inches	
Symbol	Min	Max	Min	Max
Α	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
С	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550	REF.	0.061	REF.
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
е	1.500	TYP.	0.060	TYP.
e1	3.000	TYP.	0.118	TYP.
L	0.900	1.200	0.035	0.047

Suggested Pad Layout



Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
CXT5551	SOT-89	1000



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